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|  | <h2>SI1404BDH-T1-E3</h2> |
| | <p>Hersteller-Teilenummer: SI1404BDH-T1-E3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 1.9A SOT363</p> <p>Datenblätter:  SI1404BDH-T1-E3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 12666 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

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| Teilenummer | SI1404BDH-T1-E3 |
| Hersteller | Electro-Films (EFI) / Vishay |
| Beschreibung | MOSFET N-CH 30V 1.9A SOT363 |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs , |
| Teilstatus | 12666 pcs Stock |
| Hersteller Standard Vorlaufzeit | 13 Weeks |
| detaillierte Beschreibung | N-Channel 30V 1.9A (Ta), 2.37A (Tc) 1.32W (Ta), |
| Serie | TrenchFET® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | 6-TSSOP, SC-88, SOT-363 |
| Supplier Device-Gehäuse | SC-70-6 (SOT-363) |
| Verlustleistung (max) | 1.32W (Ta), 2.28W (Tc) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 30V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 1.9A (Ta), 2.37A (Tc) |
| Rds On (Max) @ Id, Vgs | 238 mOhm @ 1.9A, 4.5V |
| VGS (th) (Max) @ Id | 1.3V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 2.7nC @ 4.5V |
| Eingabekapazität (Ciss) (Max) @ Vds | 100pF @ 15V |
| Antriebsspannung (Max Rds On, Min Rds On) | 2.5V, 4.5V |
| Vgs (Max) | ±12V |
| Verpackung | Tape & Reel (TR) |
| Bleifreier Status / RoHS-Status | Lead free / RoHS Compliant |
| Feuchtigkeitsempfindlichkeitsniveau (MSL) | 1 (Unlimited) |

SI1404BDH-T1-E3 ist neu im Original, Suche SI1404BDH-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1404BDH-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI1404BDH-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

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|---|---|--|---|
|  <p>SI1404BDH-T1-E3 Vishay / Siliconix MOSFET N-CH 30V 1.9A SOT363</p> |  <p>SI1404DH-T1-GE3 V SI1404DH-T1-GE3 V</p> |  <p>SI1404DH-T1-E3 VISHAY SI1404DH-T1-E3 VISHAY</p> |  <p>SI1403DL-T1-GE3 Vishay Precision Group SI1403DL-T1-GE3 VISHAY</p> |
|  <p>SI1404BDH-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 1.9A SOT363</p> |  <p>SI1404BDH-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 1.9A SOT363</p> |  <p>SI1403DL VISHAY SI1403DL VISHAY</p> |  <p>SI1404DH-T1 VISHAY SI1404DH-T1 VISHAY</p> |

heiße Teile

Mehr

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|--------------------|--------------------|--------------------|--------------------|--------------------|
| ⊕ SI1317DL-T1-GE3 | ↔ SI1317DL-T1-GE3 | ⇒ SI1330EDL-T1-E3 | D SI1330EDL-T1-E3 | ↔ SI1330EDL-T1-GE3 |
| ⊖ SI1330EDL-T1-GE3 | ⊕ SI1400DL-T1 | D SI1400DL-T1-E3 | ⇒ SI1400DL-T1-E3 | ↔ SI1400DL-T1-GE3 |
| ⊕ SI1400DL-T1-GE3 | ⊖ SI1401EDH-T1-GE3 | ⊕ SI1401EDH-T1-GE3 | ↔ SI1402DH-T1-GE3 | ↔ SI1402DH-T1-GE3 |
| D SI1403BDL-T1-E3 | ⊕ SI1403BDL-T1-E3 | ⊖ SI1403BDL-T1-GE3 | ⊕ SI1403BDL-T1-GE3 | ↔ SI1403CDL-T1-GE3 |
| ⇒ SI1403CDL-T1-GE3 | ↔ SI1403DL | ⊕ SI1403DL-T1 | ⊖ SI1403DL-T1-E3 | ↔ SI1403DL-T1-GE3 |
| ↔ SI1404BDH-T1-E3 | ⇒ SI1404DH-T1 | D SI1404DH-T1-E3 | ⊕ SI1404DH-T1-GE3 | ⊖ SI1404DL-T1-GE3 |
| ⊕ SI1405BDH-T1-E3 | D SI1405BDH-T1-E3 | ⇒ SI1405BDH-T1-GE3 | ↔ SI1405BDH-T1-GE3 | ↔ SI1405DL-T1 |
| ⊖ SI1405DL-T1-E3 | ⊕ SI1405DL-T1-E3 | ↔ SI1406DH | ⇒ SI1406DH-T1 | ↔ SI1406DH-T1-E3 |
| ⊕ SI1406DH-T1-E3 | ⊖ SI1406DH-T1-GE3 | ⊕ SI1406DH-T1-GE3 | D SI1407DL | ↔ SI1407DL-T1 |
| ↔ SI1407DL-T1-E3 | ⊕ SI1407DL-T1-GE3 | ⊖ SI1410EDH | ⊕ SI1410EDH-T1 | ↔ SI1410EDH-T1-E3 |

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